

Schottky Barrier Diode

RB415D

●Applications

Low current rectification (cathode common twin model)

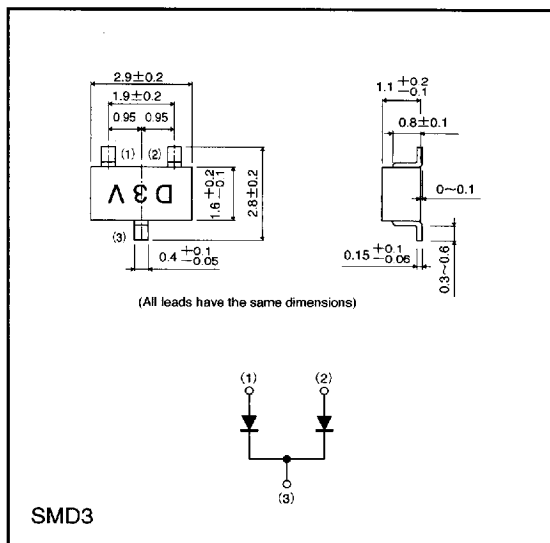
●Features

- 1) Compact mold model (SMD3)
- 2) High reliability
- 3) Two diodes with common cathode for excellent installation efficiency.

●Construction

Silicon epitaxial

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	25	V
Mean rectifying current *1	I_O	0.4	A
Peak forward surge current *2	I_{FSM}	2	A
Junction temperature	T_J	125	°C
Storage temperature	T_{stg}	-40~+125	°C
Operating temperature	T_{opr}	-30~+85	°C

*1 Mean output current per element: $I_O/2$

*2 60 Hz for 1 ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F (1)$	—	0.24	0.30	V	$I_F=100mA$
	$V_F (2)$	—	0.38	0.50	V	$I_F=200mA$
Reverse current	I_R	—	18	70	μA	$V_R=25V$

* Special precautions required concerning static electricity when being handled.

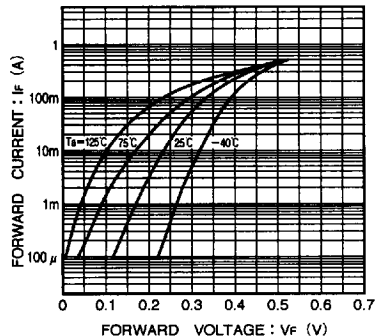
● Electrical characteristic curves ($T_a=25^\circ\text{C}$)

Fig. 1 Forward temperature characteristic

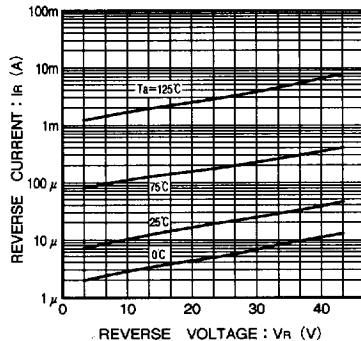


Fig. 2 Reverse temperature characteristic

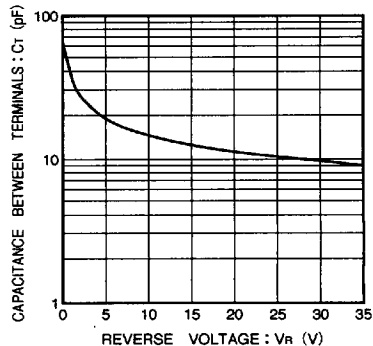


Fig. 3 Capacitance between terminals characteristic